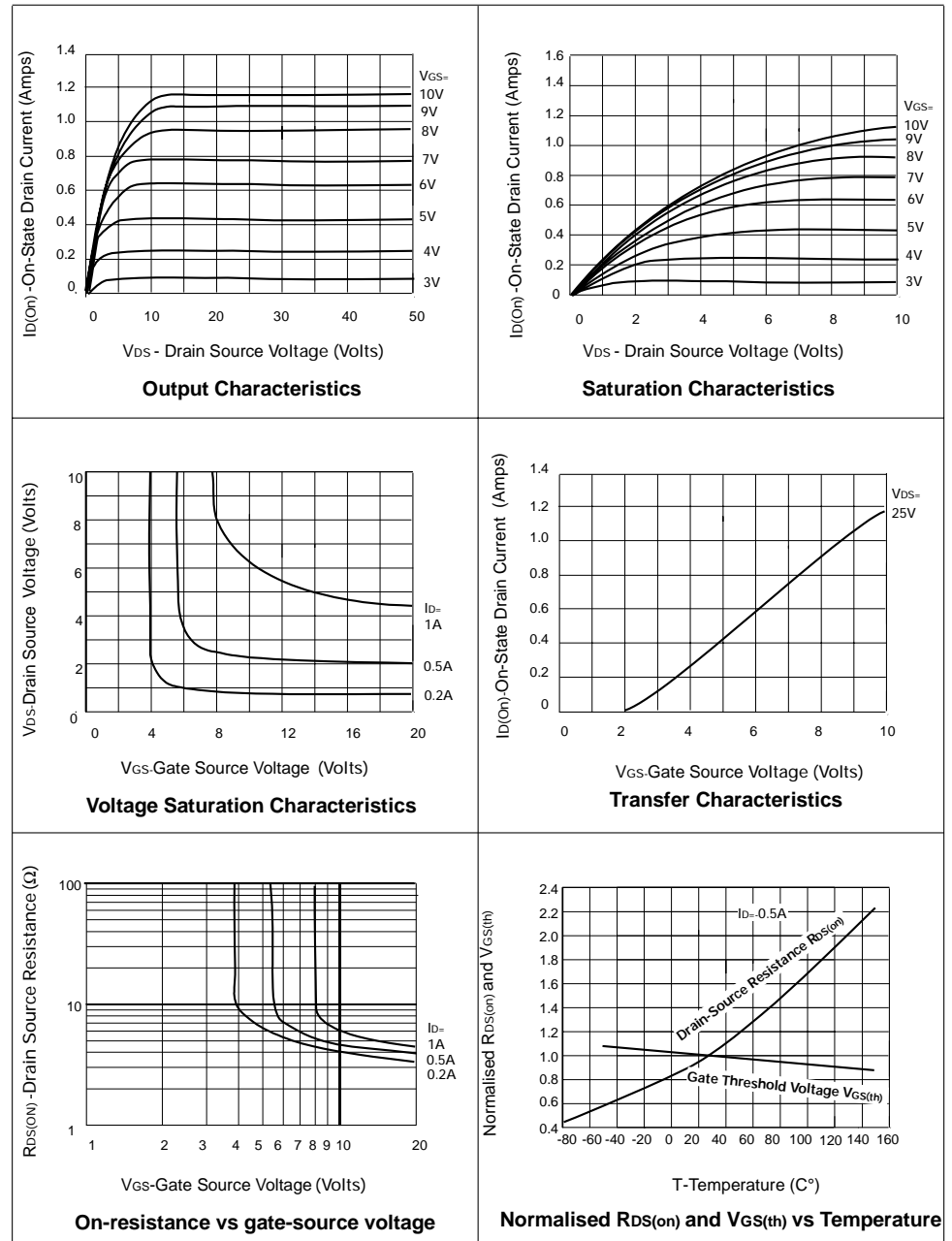




**THE DATASHEET OF
ZVN3310ASTZ**



TYPICAL CHARACTERISTICS



ZVN3310A

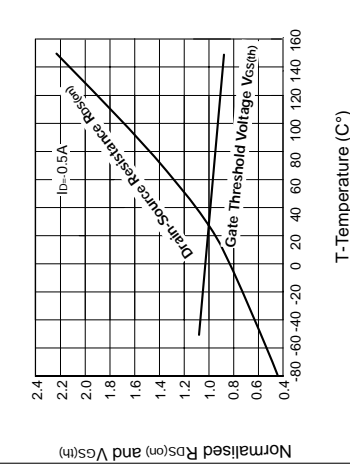
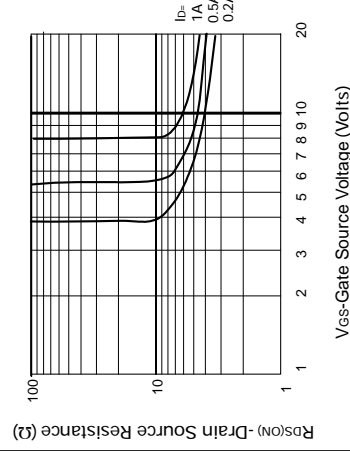
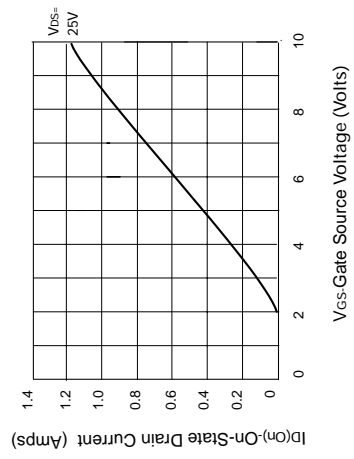
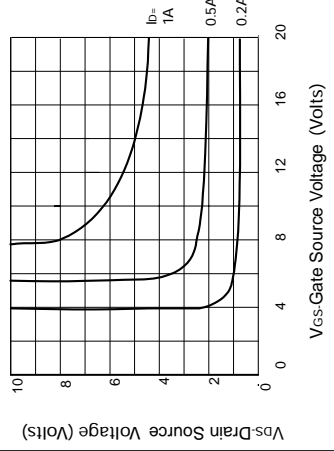
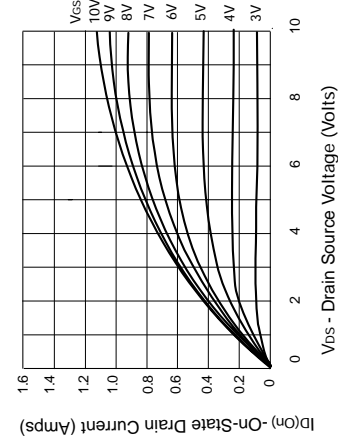
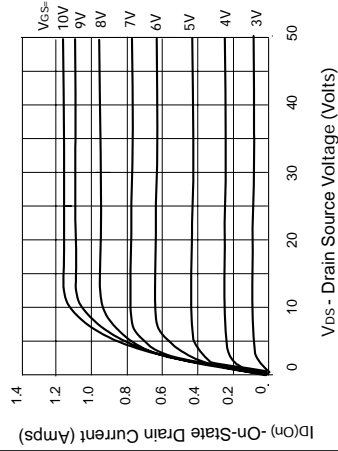
N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

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FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)} = 10\Omega$

TYPICAL CHARACTERISTICS



ABSOLUTE MAXIMUM RATINGS

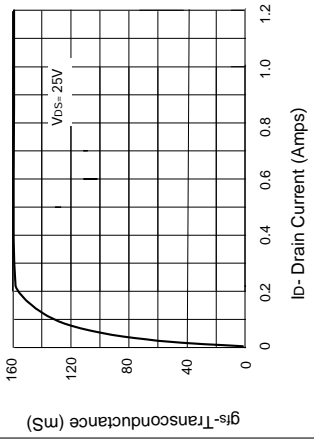
PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb}=25^{\circ}C$
Pulsed Drain Current
Gate-Source Voltage
Power Dissipation at $T_{amb}=25^{\circ}C$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

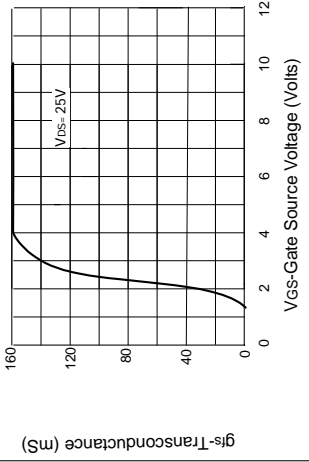
PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance(1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{rss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

ZVN3310A

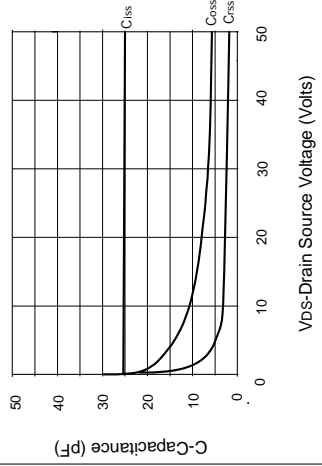
TYPICAL CHARACTERISTICS



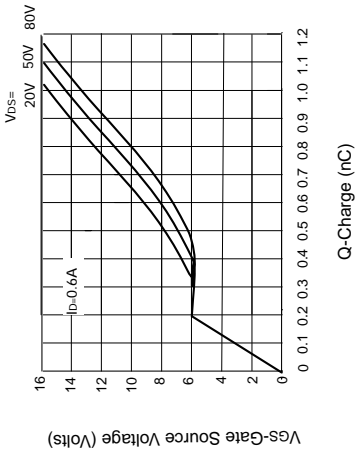
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage

Looking for pricing, stock, or lifecycle information?

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 [Diodes Incorporated](#) Information

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-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management